Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1 BRS	L1	718	LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:52			0
2 BRS	L2	51	lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:54			0
3 BRS	L3	60	lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:56			0
4 BRS	L4	736	1 or 2 or 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:09			0
5 BRS	L5	17987	LDD or "LDD" or ((light$3 adj dop$3) adj (source$1 or drain$1)) or (lightly-doped adj (source$1 or drain$1)) or ((shallow or extension$1) near4 (source$1 or drain$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:15			0
6 BRS	L6	103	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:15			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error ors
7 BRS	L7	479	LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1).	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:03			0
8 BRS	L8	74	lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:04			0
9 BRS	L9	0	lateral$4 adj diffus$5 adj double adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:05			0
10 BRS	L10	177	lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:06			0
11 BRS	L11	0	lateral$4 adj diffus$5 adj double adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:07			0
12 BRS	L12	716	7 or 8 or 9 or 10 or 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:08			0
13 BRS	L13	497	5 and 12					0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Definition	Errors
14 BRS	L14	152128	(gate$1 or electrode$1) and source$1 and drain$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:10			0
15 BRS	L15	140632	(field adj (oxide or isolat$5)) or LOCOS or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:29			0
16 BRS	L16	197	13 and 14 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:14			0
17 BRS	L17	140776	(field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:30			0
18 BRS	L20	249	lateral$4 near7 (metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:57			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
19 BRS	L21	7623	lateral$4 near7 (MOS$4 or MOSFET$1 or NMOS$4 or PMOS$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:59		Trunc ation Overf low. Retur n Serve r is: 5,0,0 LAT	n strin g from n 1
20 BRS	L22	2317	lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:01			0
21 BRS	L23	3309	4 or 12 or 18 or 19 or 20 or 22	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:02			0
22 BRS	L24	991	23 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:03			0
23 BRS	L25	531	24 and 17 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:03			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error Errors
24 BRS	L18	10	LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:04			0
25 BRS	L19	5	LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:08			0
26 BRS	L26	2371	23 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:33			0
27 BRS	L27	1176	26 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:34			0

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Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1 BRS	L1	718	LDMOS$2 or LD-MOS$2 or (LD adj MOS$3) or LDMOSFET$1 or LD-MOSFET$1 or (LD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:52			0
2 BRS	L2	51	lateral$4 adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:54			0
3 BRS	L3	60	lateral$4 adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:56			0
4 BRS	L4	736	1 or 2 or 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:09			0
5 BRS	L5	17987	LDD or "LDD" or ((light$3 adj dop$3) adj (source$1 or drain$1)) or (lightly-doped adj (source$1 or drain$1)) or ((shallow or extension$1) near4 (source$1 or drain$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:15			0
6 BRS	L6	103	4 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 16:15			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
7 BRS	L7	479	LDDMOS$2 or LDD-MOS$2 or (LDD adj MOS$3) or LDDMOSFET$1 or LDD-MOSFET$1 or (LDD adj MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:03			0
8 BRS	L8	74	lateral$4 adj double adj diffus$5 adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:04			0
9 BRS	L9	0	lateral$4 adj diffus$5 adj double adj metal adj oxide adj semiconduct$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:05			0
10 BRS	L10	177	lateral$4 adj diffus$5 adj double adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:06			0
11 BRS	L11	0	lateral$4 adj double adj diffus$5 adj (MOS$3 or MOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:07			0
12 BRS	L12	716	7 or 8 or 9 or 10 or 11	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:08			0
13 BRS	L13	497	5 and 12					0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Error ors
14 BRS	L14	152128	(gate$1 or electrode$1) and source$1 and drain$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:10			0
15 BRS	L15	140632	(field adj (oxide or isolat$5)) or LOCOS or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:29			0
16 BRS	L16	197	13 and 14 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:14			0
17 BRS	L17	140776	(field adj (oxide$1 or isolat$5)) or LOCOS$2 or trench$2 or STI$1 or (shallow adj trench$2 adj isolat$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:30			0
18 BRS	L18	10	LDPMOS$2 or LD-PMOS$2 or (LD adj PMOS$3) or LDPMOSFET$1 or LD-PMOSFET$1 or (LD adj PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:53			0
19 BRS	L19	5	LDNMOS$2 or LD-NMOS$2 or (LD adj NMOS$3) or LDNMOSFET$1 or LD-NMOSFET$1 or (LD adj NMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:54			0
20 BRS	L20	249	lateral$4 near7 (metal adj oxide adj semiconduct$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:57			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments Definition	Error Errors
21 BRS	L21	7623	lateral$4 near7 (MOS$4 or MOSFET$1 or NMOS$4 or PMOS$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 17:59	Truncation Overflow. Return string 1 from Server is: 5.0.0 IAT	
22 BRS	L22	2317	lateral$4 near7 (MOS or MOSFET$1 or NMOS or NMOSFET$1 or PMOS or PMOSFET$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:01		0
23 BRS	L23	3309	4 or 12 or 18 or 19 or 20 or 22	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:02		0
24 BRS	L24	991	23 and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:03		0
25 BRS	L25	531	24 and 17 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/03/13 18:03		0

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